

MOS FIELD EFFECT TRANSISTOR

2SK1398

N-CHANNEL MOS FET FOR HIGH SPEED SWITCHING

***** DESCRIPTION

The 2SK1398 is N-channel MOS Field Effect Transistor designed for a high-speed switching device in digital circuits. The 2SK1398 is driven by a 2.5-V power source, it is suitable for applications including headphone stereos which need power saving.

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK1398	SST

FEATURES

- Directly driven by ICs having a 3-V power supply.
- Not necessary to consider driving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the bias resistor.
- Can be used complementary with the 2SJ184.

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs= 0 V)	Vdss	50	V
Gate to Source Voltage (VDS= 0 V)	Vgss	±7.0	V
Drain Current (DC)	D(DC)	±100	mA
Drain Current (pulse) ^{Note}	D(pulse)	±200	mA
Total Power Dissipation	Рт	250	mW
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note $PW \le 10 \text{ ms}$, Duty cycle $\le 50 \%$

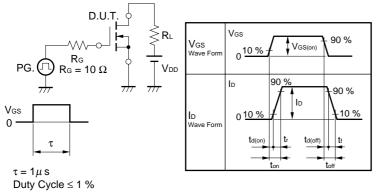
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ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

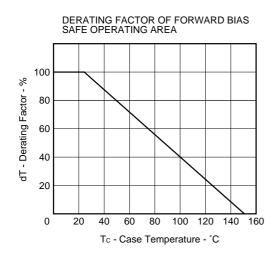
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CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Cut-off Current	IDSS	Vds = 50 V, Vgs = 0 V			10	μA
Gate Leakage Current	lgss	$V_{GS} = \pm 7.0 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			±5.0	μA
Gate to Source Cut-off Voltage	VGS(off)	$V_{DS} = 3.0 \text{ V}, \text{ Id} = 1.0 \ \mu\text{A}$	0.9	1.2	1.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 3.0 V, I _D = 10 mA	20	38		mS
Drain to Source On-state Resistance	RDS(on)1	Vgs = 2.5 V, Id = 10 mA		22	40	Ω
	RDS(on)2	Vgs = 4.0 V, Id = 10 mA		14	20	Ω
Input Capacitance	Ciss	V _{DS} = 3.0 V		8		pF
Output Capacitance	Coss	V _{GS} = 0 V		7		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		3		pF
Turn-on Delay Time	td(on)	Vdd = 3.0 V		15		ns
Rise Time	tr	ID = 20 mA		100		ns
Turn-off Delay Time	t _{d(off)}	V _{GS(on)} = 3.0 V		30		ns
Fall Time	tr	R _G = 10 Ω, R∟ = 150 Ω		35		ns

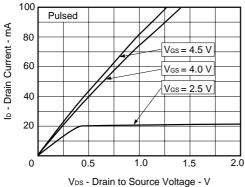
TEST CIRCUIT SWITCHING TIME

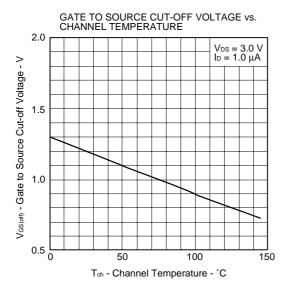


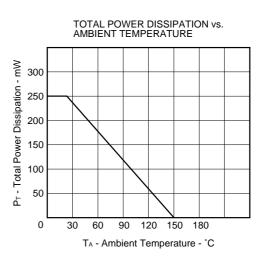
TYPICAL CHARACTERISTICS (TA = 25 °C)



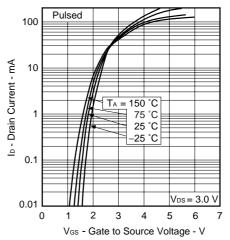




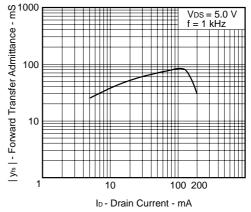




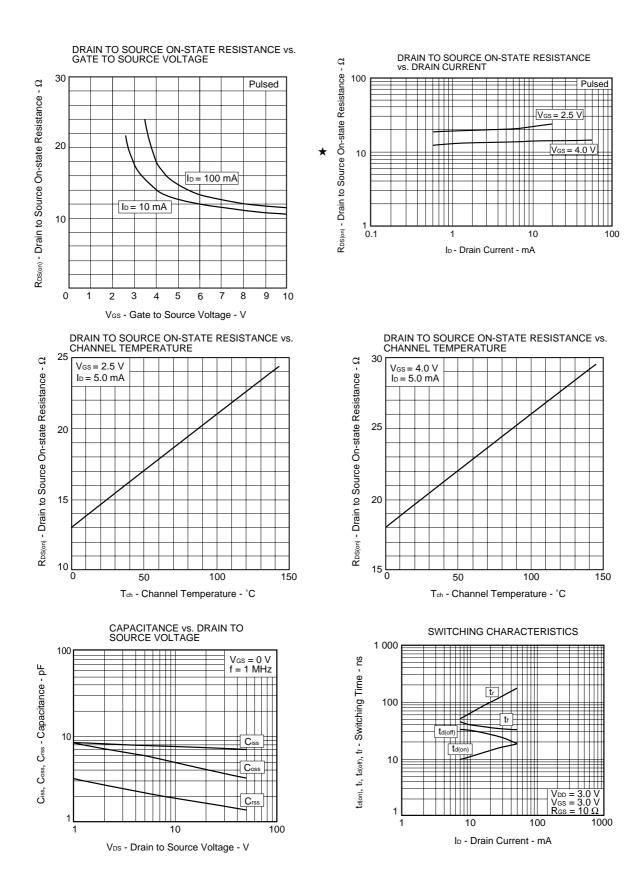
FORWARD TRANSFER CHARACTERISTICS



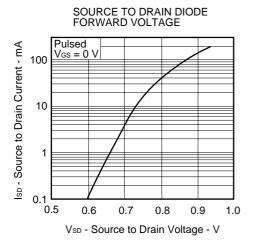
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



Data Sheet D14772EJ2V0DS00

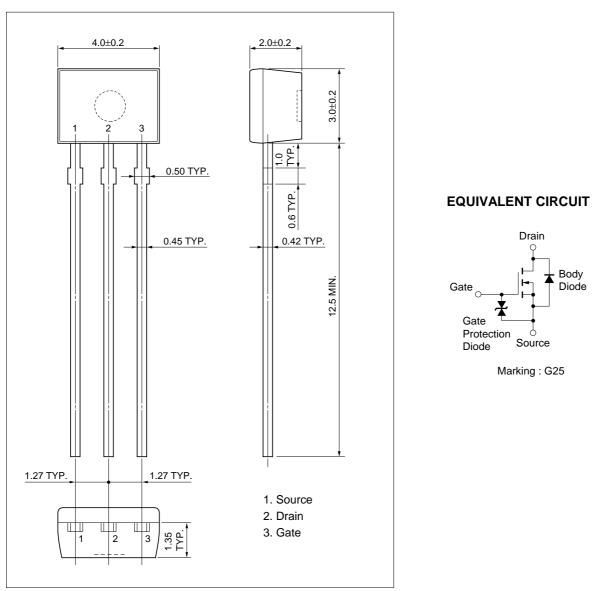


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PACKAGE DRAWING (Unit: mm)

SST



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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